



# NATIONAL INSTITUTE OF TECHNOLOGY, TIRUCHIRAPPALLI

## DEPARTMENT OF ELECTRICAL & ELECTRONICS ENGINEERING

COURSE PLAN – PART I			
Name of the programme and specialization	B.Tech. – Electrical and Electronics Engineering		
Course Title	Electron Devices		
Course Code	EEPC10	No. of Credits	03
Course Code of Pre-requisite subject(s)	Basic Physics		
Session	January 2019	Section (if, applicable)	A&B
Name of Faculty	Dr. M Sahoo	Department	EEE
Official Email	sahoo@nitt.edu	Telephone No.	
Name of Course Coordinator(s) (if, applicable)	NA		
Official E-mail	NA	Telephone No.	NA
Course Type (please tick appropriately)	<input checked="" type="checkbox"/> Core course	<input type="checkbox"/> Elective course	
<b>Syllabus (approved in BoS)</b>			
<ul style="list-style-type: none"> <li>• Semi-conductors – charge carriers, electrons and holes in intrinsic and extrinsic semi-conductors –Hall effect.</li> <li>• Diodes – PN junction – current equation – Junction Capacitance – breakdown characteristics of Zener diode, Tunnel diode, Schottky diode.</li> <li>• Bipolar junction transistors – Characteristics – Analysis of CB, CE, CC amplifier configurations.</li> <li>• Unipolar devices – FET, MOSFET, UJT and Opto-Electronic devices – theory and characteristics.</li> <li>• Rectifiers and switched mode power supplies – theory and design, filter circuits, applications.</li> </ul>			
<b>COURSE OBJECTIVES</b>			
To educate on the construction and working of common electronic devices and to prepare for application areas.			
<b>MAPPING OF COs with POs</b>			
<b>Course Outcomes:</b> Upon completion of the course, the student will be able to	<b>Programme Outcomes (PO)</b>		
1. Understand the semiconductor physics of the intrinsic, p and n materials and various devices and characteristics.	2,3,8,9		



2. Analyze simple diode circuits under DC and AC excitation.	1,2,8,9
3. Analyze and design simple amplifier circuits using BJT in CE, CC and CB configurations.	1,2,8,9
4. Understand the analysis and salient features of CE, CC & CB amplifier circuits.	1,2,3,8,9
5. Understand the construction and characteristics of FET, MOSFET and UJT.	1,2,3,8,9

**COURSE PLAN – PART II**

**COURSE OVERVIEW**

The basic understanding of electronics devices is established by studying the semiconductor material like p-type and n-type material. After knowing the material, PN junction semiconductor devices will be discussed which is necessary to understand the construction of devices like diode, BJT, FET. Operation of these devices along with its input and output characteristics will be discussed. After understanding the devices, some of its applications like rectifiers, switched mode power supplies, filter circuit etc. will be discussed.

**COURSE TEACHING AND LEARNING ACTIVITIES**

S.No.	Week/Contact Hours	Topic	Mode of Delivery
1	2 <sup>nd</sup> week of January '19 (7-11) 3 hrs	Introduction to the course, semiconductor	Lecture/Tutorial Chalk &Talk
2	3 <sup>rd</sup> week of January '19 (17-18) 2 hrs	Charge carrier, intrinsic and extrinsic semiconductor	
3	4 <sup>th</sup> week of January '19 (21-25) 3 hrs	Transportation of carrier: Drift and diffusion, Hall effect, PN Junction	
4	5 <sup>th</sup> week of January '19 (28-1 <sup>st</sup> Feb) 3 hrs	Current equation diode, characteristics, small signal model of diode, junction capacitance	
5	2 <sup>nd</sup> week of February '19 (04-08) 3 hrs	Zener diode: break down characteristics, tunnel diode, Schottky diode	
6	3 <sup>rd</sup> week of February '19 (11-15) 3 hrs	Application of diode	



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7	4 <sup>th</sup> week of February '19 (18-22) 3 hrs	Introduction to BJT, types of BJT. its operation and characteristics	Lecture/Tutorial Chalk &Talk
8	5 <sup>th</sup> week of February '19 (25-1 <sup>st</sup> March)	BJT: Analysis of CB, CE, CC amplifier configuration	
9	1 <sup>st</sup> week of March '19 (04-08) 3 hrs	BJT: Analysis of CB, CE, CC amplifier configuration	
10	2 <sup>nd</sup> week of March '19 (11-15) 3 hrs	Introduction to FET, MOSFET, construction	
11	3 <sup>rd</sup> week of March '19 (18-22) 3 hrs	Operation of MOSFET and its characteristics	
12	4 <sup>th</sup> week of March '19 (25-29) 3 hrs	Operation of MOSFET and its characteristics	
13	1 <sup>st</sup> week of April '19 (01-05) 3 hrs	Switched mode power supplies, theory and design	
14	2 <sup>nd</sup> week of April '19 (08-12) 3 hrs	Filter circuits	

### Course Assessment Methods

S.No.	Mode of Assessment	Week/Date	Duration	% Weightage
1	Assessment-1 (CT-1) (Written Test)	4 <sup>th</sup> week of February '19 25/02/2019	1 hr	20
2	Assessment-2 (CT-2) (Written Test)	3 <sup>rd</sup> week of April '19, 18/04/2019	1 hr	20
3	Assessment-3 (2 Nos. Each for 10 marks- Surprize/Quiz Tests)	During regular Classes	1 hr	20
4 (CPA)	Compensation Assessment* (Written Test)	4 <sup>th</sup> week of April '19	1 hr	20
5	Assessment-4 (End sem) (Written Test)	1 <sup>st</sup> week of May '19	2 hr	40

